

LOW LEAKAGE DIODE

Switching diode with a very low reverse current, encapsulated in a subminiature glass (DO-34) envelope.

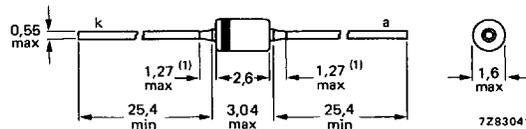
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	125 V
Forward voltage $I_F = 200 \text{ mA}$	V_F	max.	1,0 V
Reverse current $V_R = 125 \text{ V}$	I_R	max.	1,0 nA
Diode capacitance $V_R = 0; f = 1 \text{ MHz}$	C_d	max.	8,0 pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-34 (SOD-68).



(1) Lead diameter in this zone uncontrolled.

The cathode is indicated by a brown band on a black body.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	125 V
Forward current (d.c.)	I_F	max.	225 mA
Repetitive peak forward current	I_{FRM}	max.	450 mA
Non-repetitive peak forward current $t_p = 1 \mu s$	I_{FSM}	max.	4 A
Storage temperature	T_{stg}		-65 to + 175 °C
Junction temperature	T_j	max.	125 °C

THERMAL RESISTANCE

From junction to ambient in free air
mounted on a p.c. board with
a clearance of 10 mm

$R_{th j-a} = 400 \text{ K/W}$

CHARACTERISTICS

$T_j = 25 \text{ °C}$ unless otherwise specified

Reverse current under maximum light conditions
(illuminance = 500 lux)

$V_R = 125 \text{ V}$

I_R max. 1 nA

$V_R = 30 \text{ V}; T_j = 125 \text{ °C}$

I_R max. 300 nA

$V_R = 125 \text{ V}; T_j = 125 \text{ °C}$

I_R max. 500 nA

Forward voltage

$I_F = 1 \text{ mA}$

V_F 0,64 to 0,74 V

$I_F = 5 \text{ mA}$

V_F 0,70 to 0,80 V

$I_F = 50 \text{ mA}$

V_F 0,74 to 0,88 V

$I_F = 200 \text{ mA}$

V_F 0,83 to 1,00 V

Diode capacitance

$V_R = 0; f = 1 \text{ MHz}$

C_d max. 8 pF

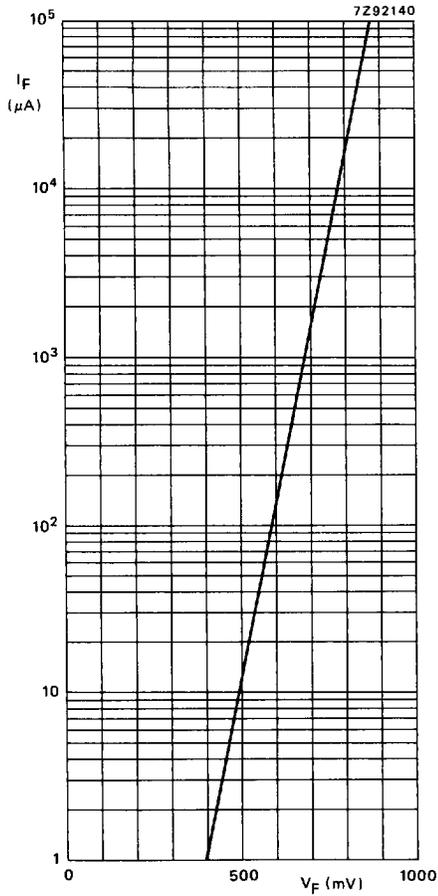


Fig. 2 $T_j = 25\text{ }^\circ\text{C}$; typical values.

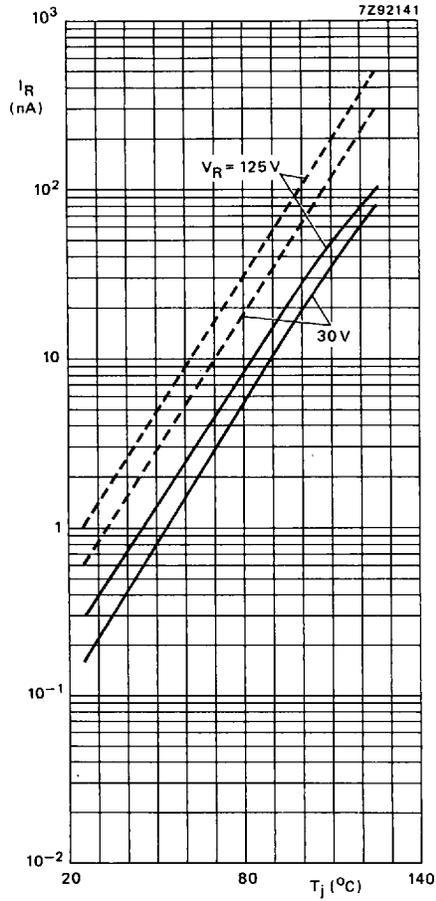


Fig. 3 --- = max. values;
 — = typ. values.

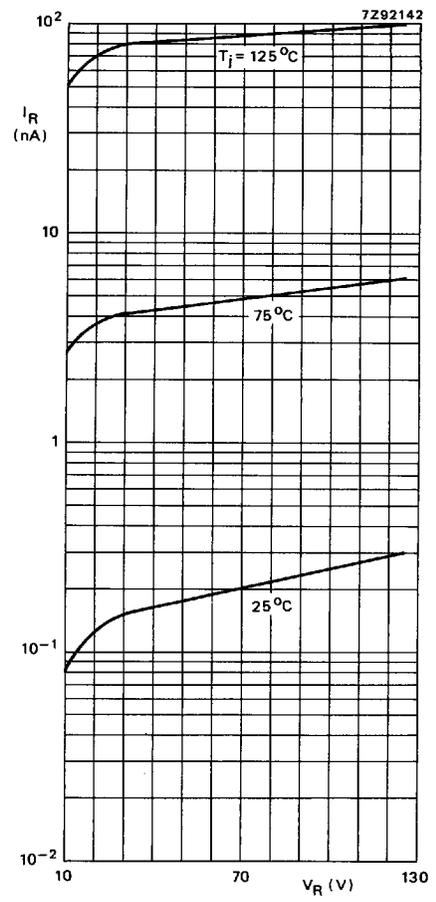


Fig. 4 Typical values.